TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSIV)

TPCA8042

Lithium-Ion Battery Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance: $RDS(ON) = 2.6 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: | Yfs | =94 S (typ.)
- Low leakage current: $IDSS = 10 \mu A (max) (VDS = 30 V)$
- Enhancement mode: $V_{th} = 1.3$ to 2.5 V ($V_{DS} = 10$ V, $I_{D} = 1$ mA)

Absolute Maximum Ratings (Ta = 25°C)

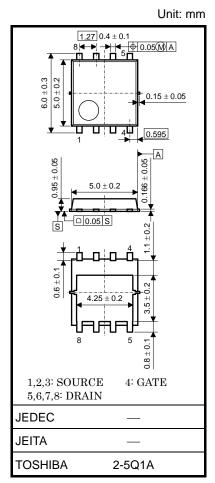
| Characte | eristic | Symbol | Rating | Unit |
|---------------------------|-------------------------------|------------------|-------------------|------|
| Drain-source voltage | | V_{DSS} | 30 | V |
| Drain-gate voltage (R | $k_{GS} = 20 \text{ k}\Omega$ | V_{DGR} | 30 | V |
| Gate-source voltage | | V_{GSS} | ±20 | V |
| Drain current | DC (Note 1) | ΙD | I _D 45 | |
| Diain current | Pulsed (Note 1) | I _{DP} | 135 | Α |
| Drain power dissipati | on (Tc=25°C) | P_{D} | 45 | W |
| Drain power dissipati | on (t = 10 s) | P _D | 2.8 | W |
| | (Note 2a) | | | |
| Drain power dissipati | on $(t = 10 s)$ | P _D | 1.6 | W |
| | (Note 2b) | | | |
| Single-pulse avalance | he energy (Note 3) | E _{AS} | 263 | mJ |
| Avalanche current | | I_{AR} | 45 | Α |
| Repetitive avalanche | energy rc=25°C) (Note 4) | E _{AR} | 4.5 | mJ |
| Channel temperature | | T _{ch} | 150 | °C |
| Storage temperature range | | T _{stg} | -55 to 150 | °C |

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Ha

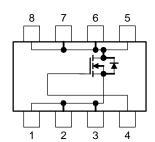
reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

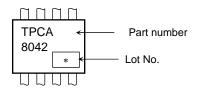
Circuit Configuration



Thermal Characteristics

| Characteristic | Symbol | Max | Unit |
|---|------------------------|------|------|
| Thermal resistance, channel to case (Tc=25°C) | R _{th (ch-c)} | 2.78 | °C/W |
| Thermal resistance, channel to ambient (t = 10 s) (Note 2a) | R _{th (ch-a)} | 44.6 | °C/W |
| Thermal resistance, channel to ambient (t = 10 s) (Note 2b) | R _{th (ch-a)} | 78.1 | °C/W |

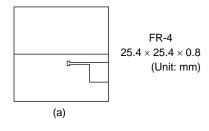
Marking (Note 5)

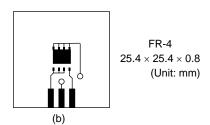


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

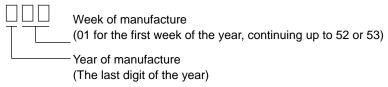




Note 3: $V_{DD} = 24 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 0.1 mH, $I_{AR} = 45 \text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)



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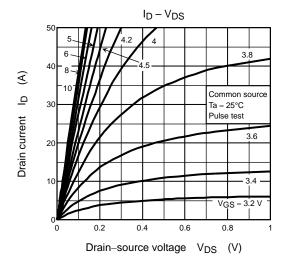
Electrical Characteristics (Ta = 25°C)

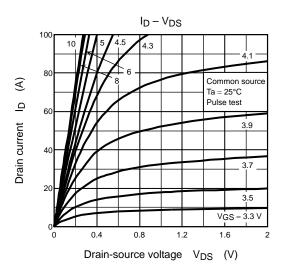
| Characteristic | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--|-----------------|----------------------|--|---|------|------|------|
| Gate leakage cui | rent | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±100 | nA |
| Drain cutoff curre | ent | I _{DSS} | V _{DS} = 30 V, V _{GS} = 0 V | _ | _ | 10 | μА |
| Drain-source bre | akdown voltago | V (BR) DSS | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$ | 30 | _ | _ | V |
| Diain-source bre | akdowii vollage | V (BR) DSX | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$ | 10 | _ | _ | V |
| Gate threshold ve | oltage | V _{th} | V _{DS} = 10 V, I _D = 1 mA | 1.3 — 2.5 — 4.0 5.7 — 2.6 3.3 47 94 — | | V | |
| Drain-source ON-resistance Forward transfer admittance | | R _{DS} (ON) | $V_{GS} = 4.5 \text{ V}, I_D = 23 \text{ A}$ | _ | 4.0 | 5.7 | - mΩ |
| | | | V _{GS} = 10 V, I _D = 23 A | _ | 2.6 | 3.3 | |
| Forward transfer | admittance | Y _{fs} | V _{DS} = 10 V, I _D = 23 A | 47 | 94 | _ | S |
| Input capacitance | 9 | C _{iss} | | _ | 2900 | _ | |
| Reverse transfer capacitance | | C _{rss} | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | _ | 460 | _ | pF |
| Output capacitance | | Coss | | _ | 800 | _ | |
| | Rise time | t _r | 10 V □ ln = 23A | | 12 | | |
| Switching time | Turn-on time | t _{on} | VGS OV J L . FOVOUT | DS = 0 V | _ | | |
| Switching time | Fall time | t _f | R. = 1 | _ | 23 | _ | - ns |
| | Turn-off time | t _{off} | | _ | 78 | _ | |
| Total gate charge (gate-source plus | ate-drain) | | | | | | |
| Gate-source charge 1 | | Q _{gs1} | $V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 45 \text{ A}$ | _ | 10 | _ | nC |
| Gate-drain ("mille | er") charge | Q _{gd} | | _ | 17 | _ | |

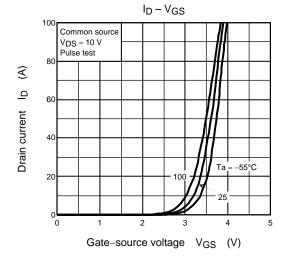
Source-Drain Ratings and Characteristics (Ta = 25°C)

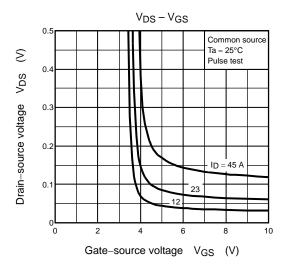
| Characteristic | | Symbol | Test Condition | Min | Тур. | Max | Unit | |
|-------------------------|-------|----------|----------------|---|------|-----|------|---|
| Drain reverse current | Pulse | (Note 1) | I_{DRP} | _ | _ | _ | 135 | Α |
| Forward voltage (diode) | | | V_{DSF} | I _{DR} = 45 A, V _{GS} = 0 V | _ | _ | -1.2 | V |

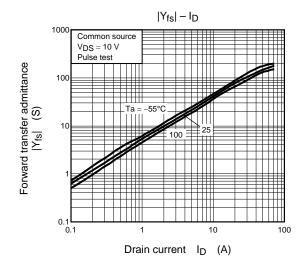
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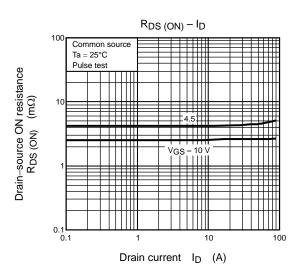




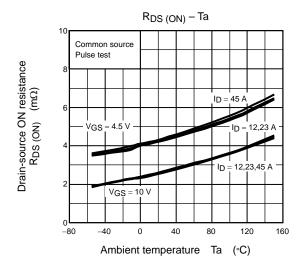


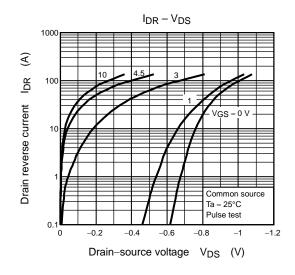


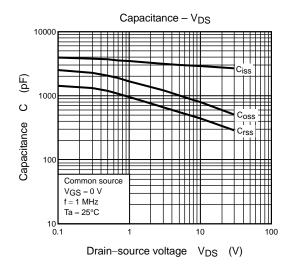


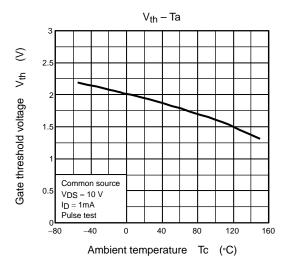


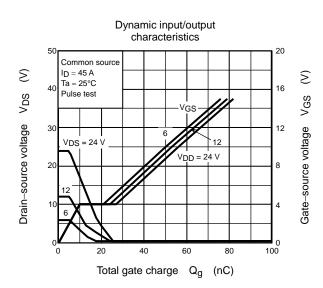
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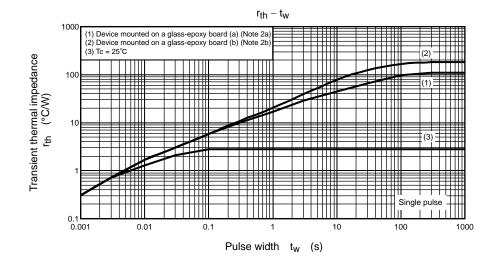


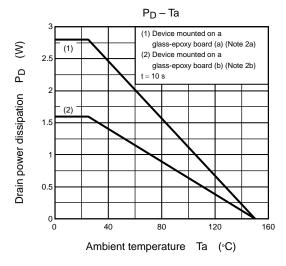


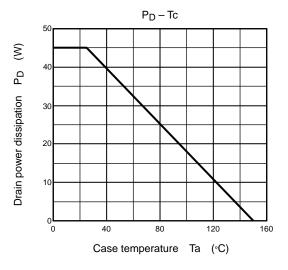


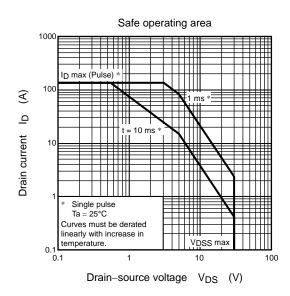


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